

# Progress on Nb<sub>3</sub>Sn and V<sub>3</sub>Si

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Nb<sub>3</sub>Sn - Nb<sub>3</sub>Sn at LNL Liquid Sn Diffusion





Nb<sub>3</sub>Sn Liquid Sn diffusion Mechanical Plating Double Magnetron Post Magnetron V<sub>3</sub>Si Thermal diffusion Thermal Diffusion + Plasma

























Nb<sub>3</sub>Sn - Nb<sub>3</sub>Sn at LNL Post Magnetron: 6 GHz Cavities

Time of sputtering:70 minAnnealing Time:1 h at 850°C

Four hypotheses:

- 1) Sn evaporation due to plasma interaction with the growing film
- 2) Too thin Film
- 3) Spurious phases presence (slow annealing ramp time)
- 4) We suspect the **substrate treatment** requires even more attention



V<sub>3</sub>Si - V<sub>3</sub>Si at LNL Thermal Diffusion

Research for the **best Chemical Treatment of V** 

- $\cdot$  SiH<sub>4</sub> Decomposition
- Si Diffusion
- $\cdot$  V<sub>3</sub>Si Nucleation
- Film Growing
- Recrystallization
- H<sub>2</sub> Removal

### Variables: T, t, p(SiH<sub>4</sub>)













1) Plasma Silanization:

 $T_c = 15.7 \text{ K}, \Delta T_c = 0.2 \text{ K}$ 

2) V<sub>3</sub>Si 6 GHz cavity obtained: Work in progress

#### Good News Allen: 6 GHz Cavities



#### **6 GHz Cavities**



- 80 cavities are under fabrication using Scrap Nb
- Flanges are seamless: no brazing, no EB welding
- It is possible to perform more than one RF test a day

## The End

NO SAMPLE IS COMPARABLE TO A CAVITY!